

STS5PF20V-VB Datasheet P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
	0.015 at $V_{GS} = -4.5 \text{ V}$	- 13 ^a			
- 20	0.021 at $V_{GS} = -2.5 \text{ V}$	- 10 ^a	20 nC		
	0.040 at V _{GS} = - 1.8 V	- 8			

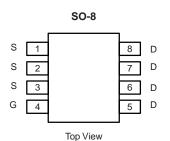
FEATURES

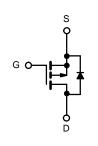
- Halogen-free According to IEC 61249-2-21 Definition

- Trench Power MOSFET 100 % $R_{\rm g}$ Tested Compliant to RoHS Directive 2002/95/EC



FREE





P-Channel MOSFET

APPLICATIONS

- Portable Devices
 - Load Switch
 - Battery Switch
 - Charger Switch

ABSOLUTE MAXIMUM RATINGS	S T _A = 25 °C, unles	ss otherwise note	ed		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 20			
Gate-Source Voltage	V_{GS}	± 12	V		
	$T_C = 25 ^{\circ}\text{C}$ $T_C = 70 ^{\circ}\text{C}$		- 13 ^a - 10 ^a		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	- 8 ^{b, c}		
T _A = 70 °C Pulsed Drain Current			- 7.1 ^{b, c} - 50	A	
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}\text{C}$ $T_A = 25 ^{\circ}\text{C}$	I _S	- 6 ^a - 2.9 ^{b, c}		
	T _C = 25 °C		19		
Maximum Power Dissipation	$T_C = 70 ^{\circ}\text{C}$ $T_A = 25 ^{\circ}\text{C}$	P _D	12 3.5 ^{b, c}	W	
	T _A = 70 °C		2.2 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature		260			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, e}	t ≤ 5 s	R _{thJA}	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	5.3	6.5	O/ VV	

Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- e. Maximum under Steady State conditions is 80 °C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•	l .	l .	
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 12		~\\/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	i _D = - 250 μA		3		mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	- 0.5		- 1.2	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 20	- 0.5 - 1 μA	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 0.5		
Zero Gate Voltage Drain Current		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1		
Zero Gate voltage Drain Current	I _{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α	
		V _{GS} = - 4.5 V, I _D = - 5.6 A		0.015			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 5.3 A		0.021		Ω	
		V _{GS} = - 1.8 V, I _D = - 2.5 A		0.040		1	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 5.6 A		35		S	
Dynamic ^b				•	l .		
Total Gate Charge	0	V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 5 A		50	75		
Cata Causa Chausa	Q_g			20	30		
Gate-Source Charge	Q _{gs}	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 5 A		3.3		nC	
Gate-Drain Charge	Q_{gd}			8.4			
Gate Resistance	R_g	f = 1 MHz	0.2	1	2	kΩ	
Turn-On Delay Time	t _{d(on)}			0.71	1.1		
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_L = 1 \Omega$		1.7	2.6		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -5 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1$		6	9		
Fall Time	t _f	Ω		3.2	5		
Turn-On Delay Time	t _{d(on)}			0.3	0.45	us	
Rise Time	t _r	V_{DD} = - 10 V, R_L = 1 Ω		0.6	0.9		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -5 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1$		10	15		
Fall Time	t _f	Ω		3.5	5.5		
Drain-Source Body Diode Characterist	ics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 6	Α	
Pulse Diode Forward Current	I _{SM}				- 50		
Body Diode Voltage	V_{SD}	I _S = - 5 A, V _{GS} = 0 V		- 0.85	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			30	60	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 6 A, dI/dt = 100 A/μs, T _{.1} = 25 °C		20	40	nC	
Reverse Recovery Fall Time	t _a	$_{iF}$ – 0 A, divut = 100 A/ μ s, $_{ij}$ = 25 $^{\circ}$ C		13		ne	
Reverse Recovery Rise Time	t _b			17		ns	

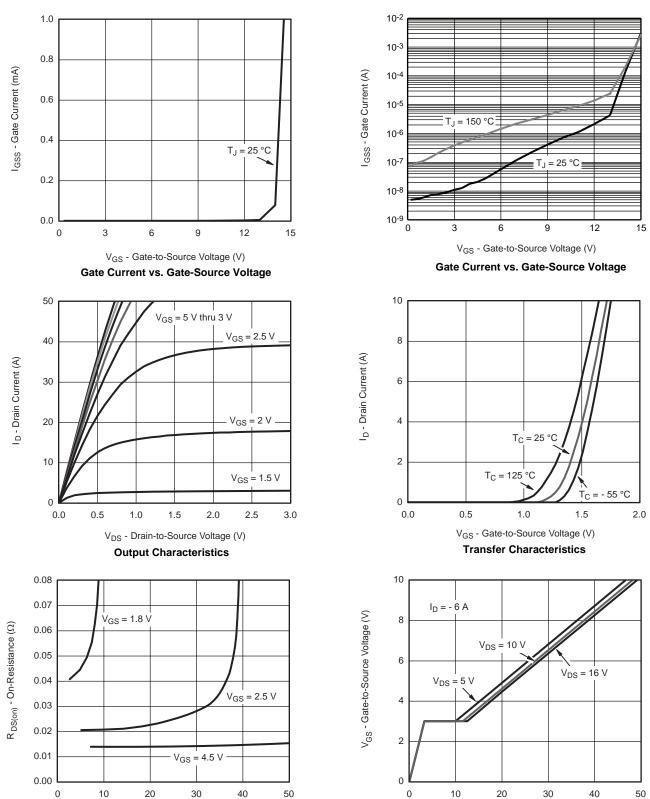
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$ b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

服务热线:400-655-8788





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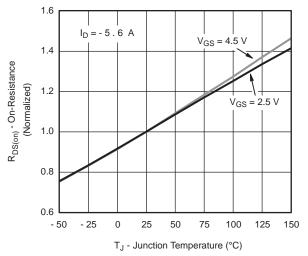
I_D - Drain Current (A)

On-Resistance vs. Drain Current

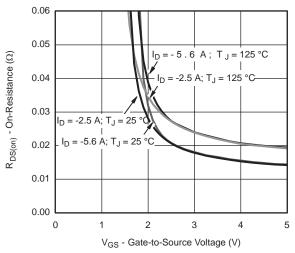
Q_q - Total Gate Charge (nC)

Gate Charge

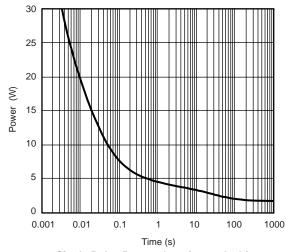




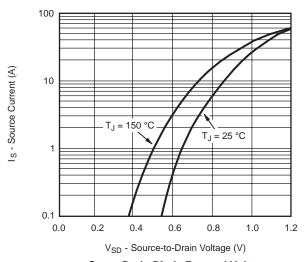
On-Resistance vs. Junction Temperature



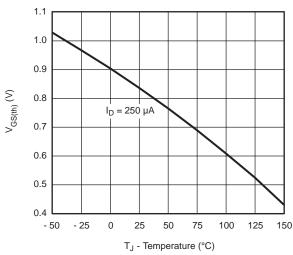
On-Resistance vs. Gate-to-Source Voltage



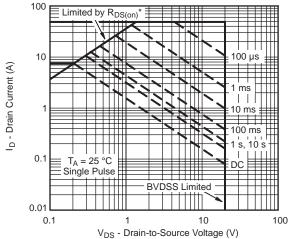
Single Pulse Power, Junction-to-Ambient



Soure-Drain Diode Forward Voltage



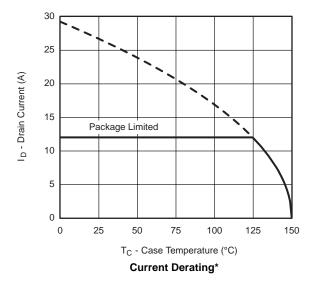
Threshold Voltage

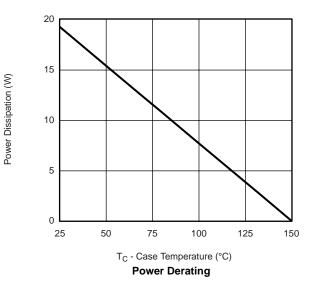


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient



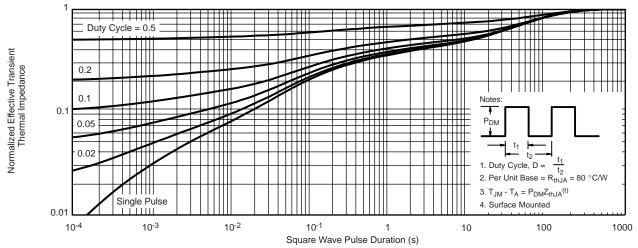




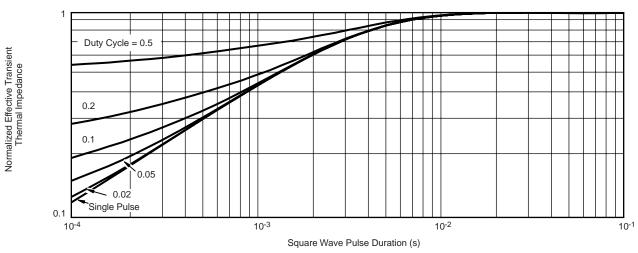
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^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





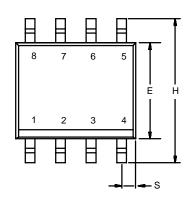
Normalized Thermal Transient Impedance, Junction-to-Ambient

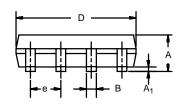


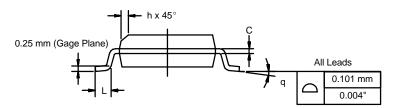
Normalized Thermal Transient Impedance, Junction-to-Case



SOIC (NARROW): 8-LEADJEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
FCN: C-06527-Rev I 11-Sen-06					

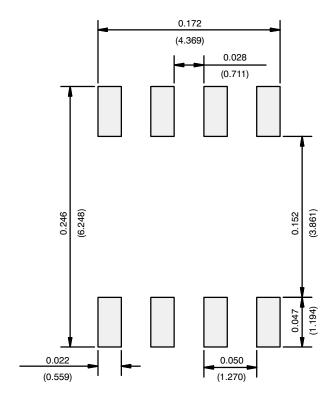
ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498

服务热线:400-655-8788



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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